

Development of Far-infrared Spectrophotometers based on Superconducting Tunnel Junction (STJ) for COBAND Experiment



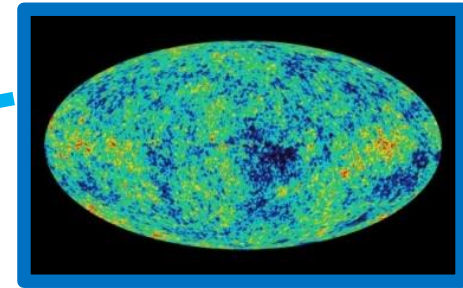
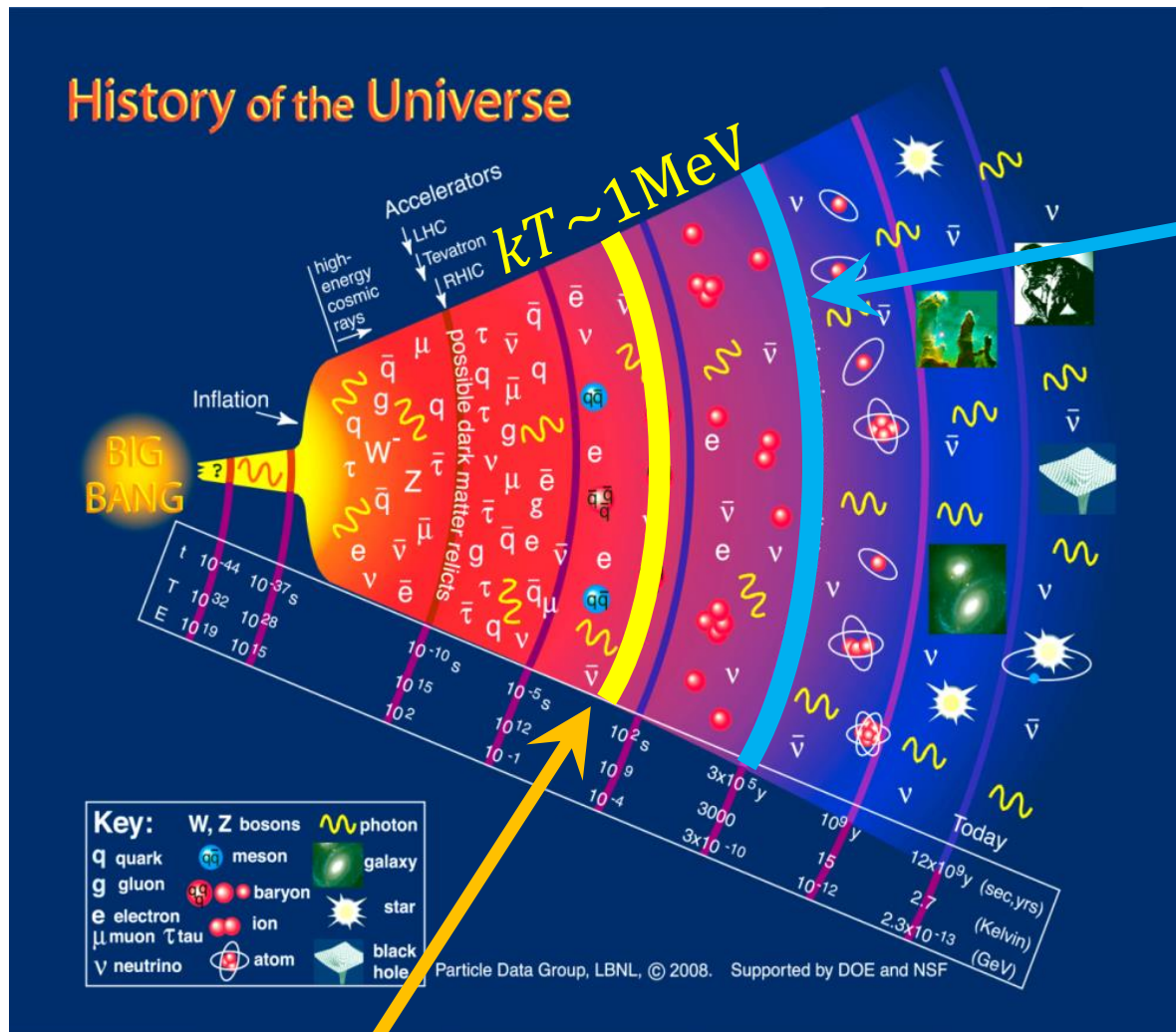
Neutrino Frontier Workshop 2017

Dec. 11-13, 2017 / Biwako Grand Hotel Tensyo, Otsu

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on behalf of COBAND Collaboration

Cosmic neutrino background (CνB)



CMB

(=Photon decoupling)

$$n_{\gamma} = 411/\text{cm}^3$$

$$T_{\gamma} = 2.73 \text{ K}$$

~380,000yrs after the Big Bang

CνB (=neutrino decoupling)
~1sec after the big bang

$$n(\nu_3 + \bar{\nu}_3) \sim 110/\text{cm}^3$$

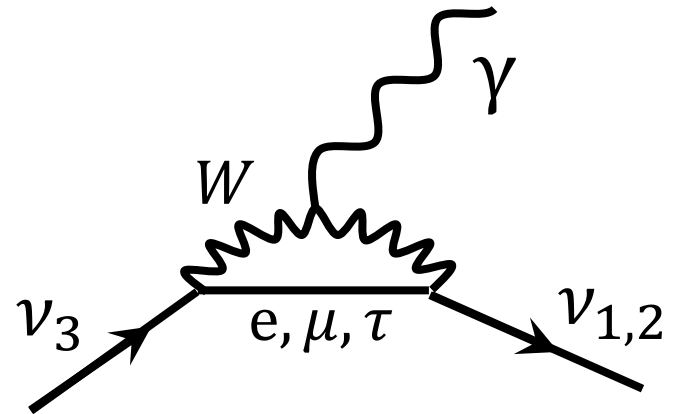
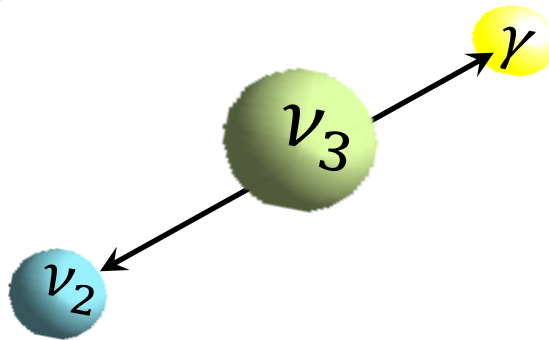
Neutrino Decay



□ Heavier neutrinos in mass-eigenstate (ν_2 , ν_3) are not stable

– Neutrino can decay through the loop diagrams

$$- \nu_3 \rightarrow \nu_{1,2} + \gamma$$



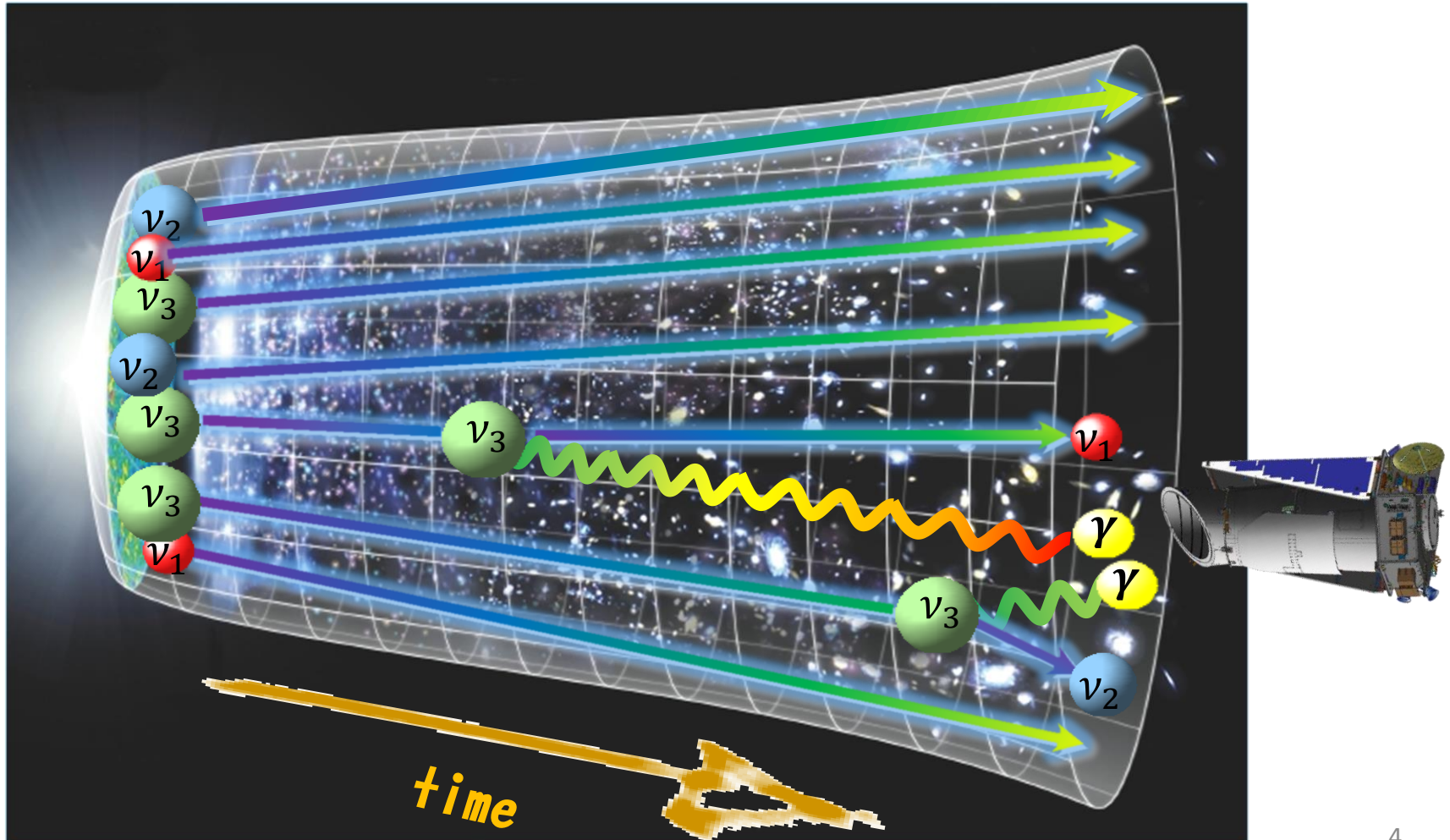
→ We search for neutrino decay using Cosmic Background Neutrino (CvB) as the neutrino source

COBAND (COsmic BAcground Neutrino Decay)



Search for **Neutrino decay** in **Cosmic background neutrino**

→ To be observed as photons in neutrino decays



COBAND Collaboration Members (As of Nov. 2017)

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Motivation of ν -decay search in $C\nu B$

ν_3 Lifetime

- Standard Model expectation: $\tau = O(10^{43})$ yrs
- Experimental lower limit: $\tau = O(10^{12})$ yrs
- L-R sym. model prediction: $\tau = O(10^{17})$ yrs

for W_L - W_R mixing angle $|\zeta| \sim 0.02$

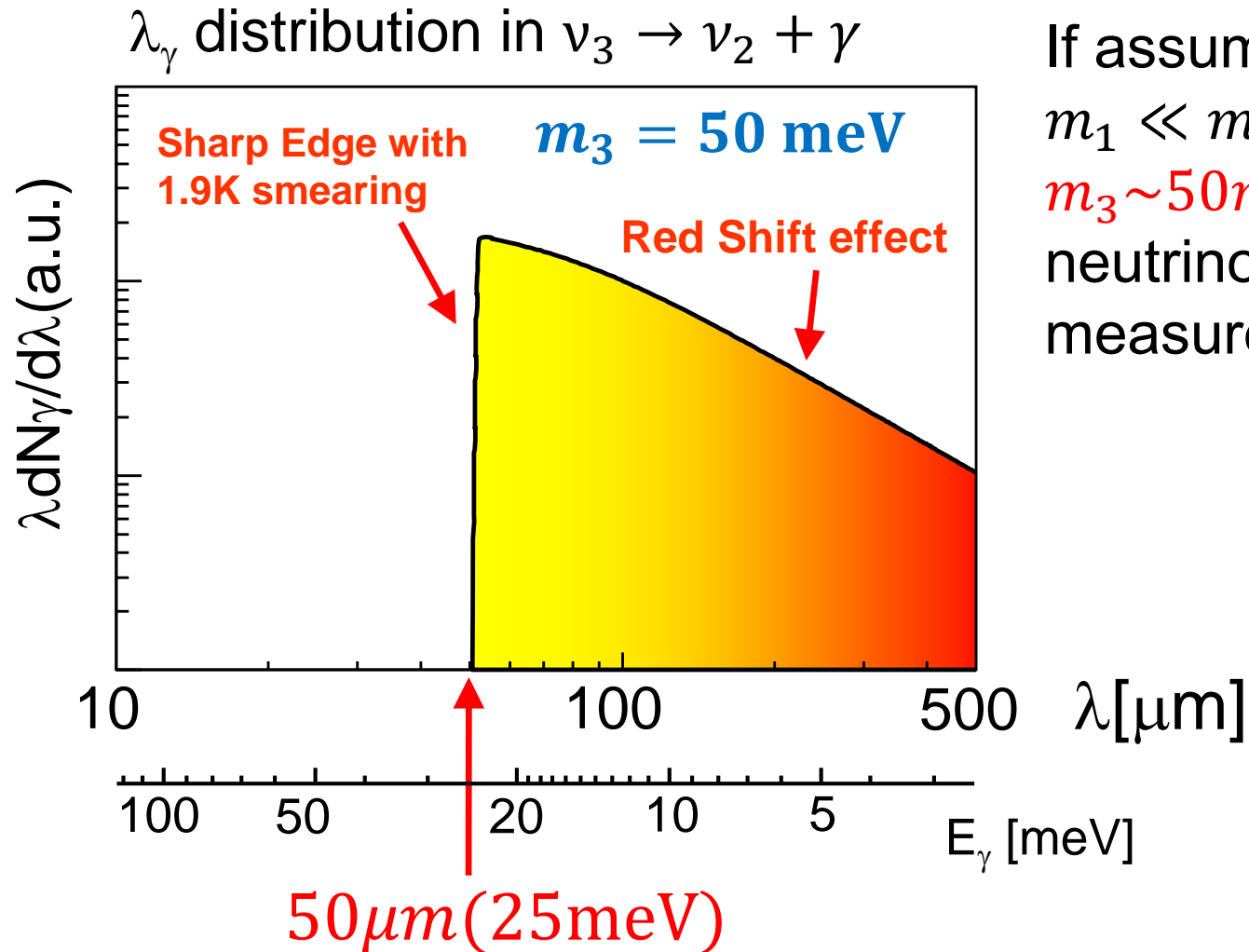
If we observed the neutrino radiative decay at the lifetime much shorter than the SM expectation, it would be

- Physics beyond the Standard Model
- Direct detection of $C\nu B$
- Determination of the neutrino mass

$$- m_3 = (m_3^2 - m_{1,2}^2)/(2E_\gamma)$$

→ Aiming at a sensitivity to ν_3 lifetime in $O(10^{13} - 10^{17})$ yrs

Expected photon wavelength spectrum from CνB decays

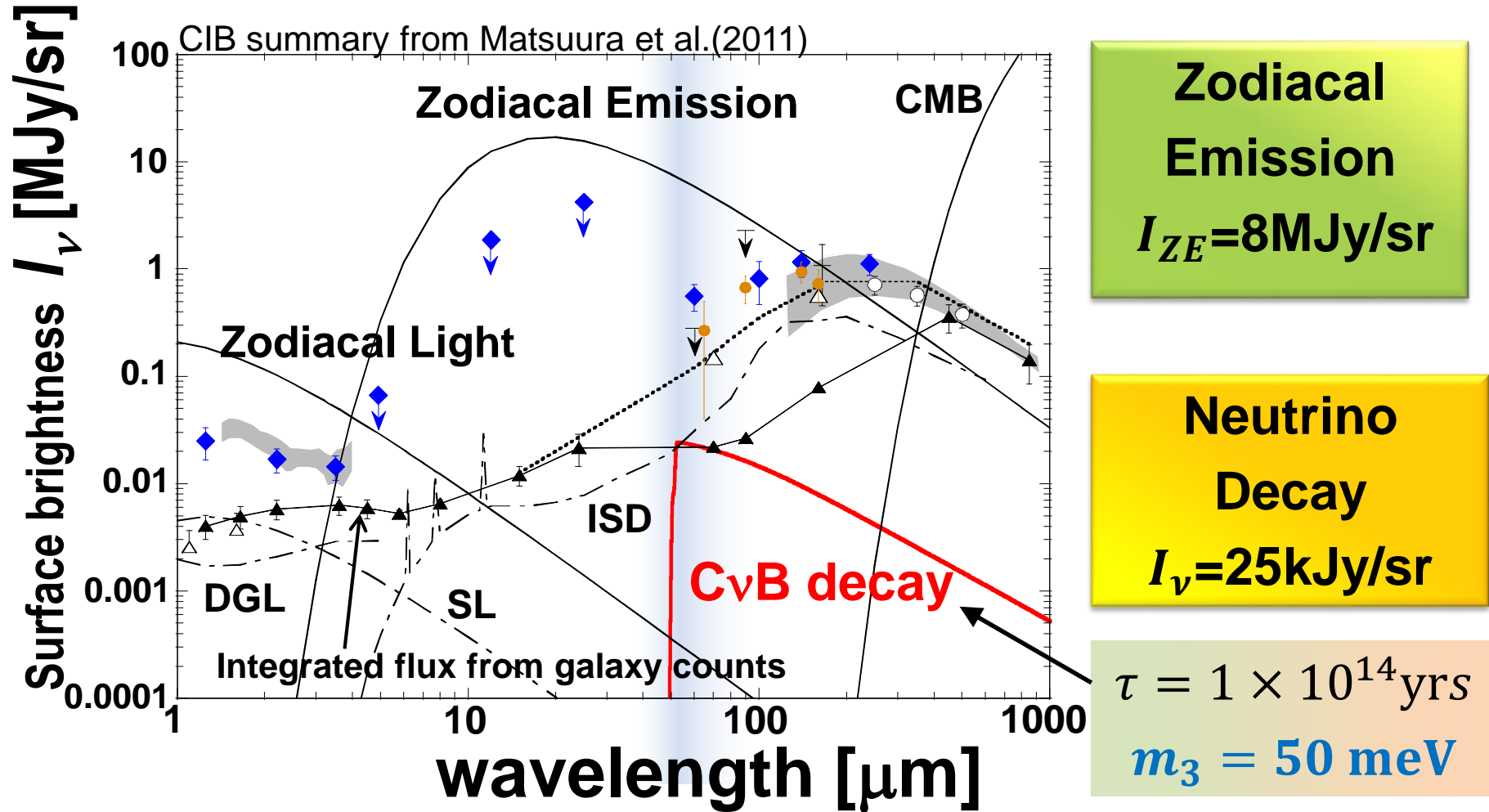


If assume

$m_1 \ll m_2 < m_3$,
 $m_3 \sim 50 \text{ meV}$ from
neutrino oscillation
measurements

No other source has such a sharp edge structure!!

Neutrino Decay signal and backgrounds



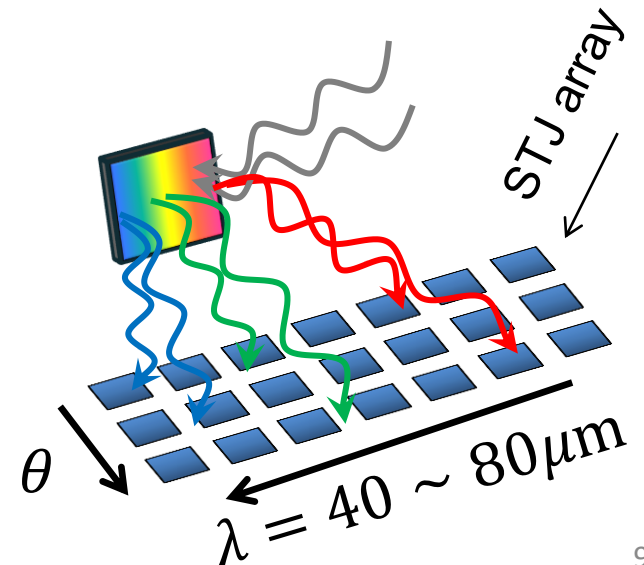
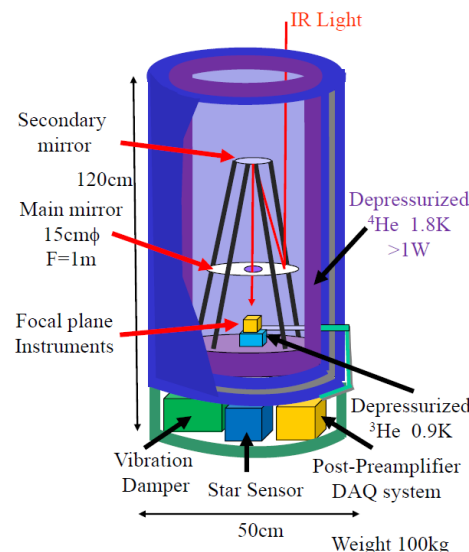
The sharp edge in the spectrum is ν decay unique signature.

Proposal for COBAND Rocket Experiment

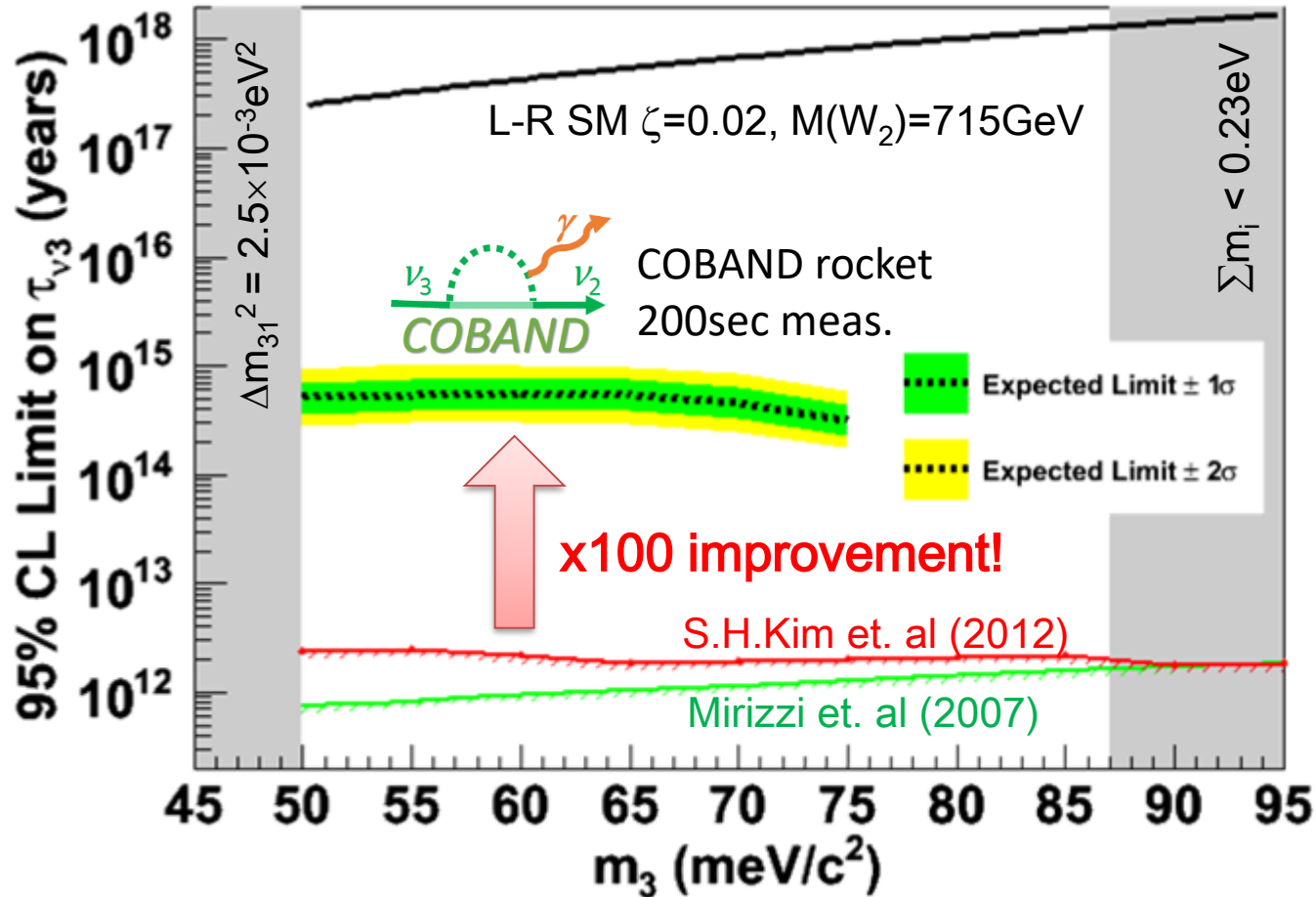
Aiming at a sensitivity to ν lifetime for $\tau(\nu_3) = 0(10^{14})$ yrs

JAXA sounding rocket S-520

- Telescope with **15cm diameter** and **1m focal length**
- At the focal point, a diffraction grating covering **$\lambda=40\text{-}80\mu\text{m}$** and an array of photo-sensor pixels of **$50(\lambda) \times 8(\theta)$** are placed.
- Each pixel has **$100\mu\text{m} \times 100\mu\text{m}$** sensitive area and ability of **single-photon detection**.



COBAND rocket experiment sensitivity



- Can set lower limit on ν_3 lifetime at $4\text{--}6 \times 10^{14}$ yrs if no neutrino decay
- If ν_3 lifetime were 2×10^{14} yrs, the signal significance would be at 5σ

Requirements for the photo-sensor in COBAND rocket experiment

- Sensitive area of $100\mu\text{m} \times 100\mu\text{m}$ for each pixel
- High detection efficiency for **a far-infrared single-photon** in $\lambda=40\mu\text{m} \sim 80\mu\text{m}$
- Dark count rate less than 300Hz (expected real photon rate)

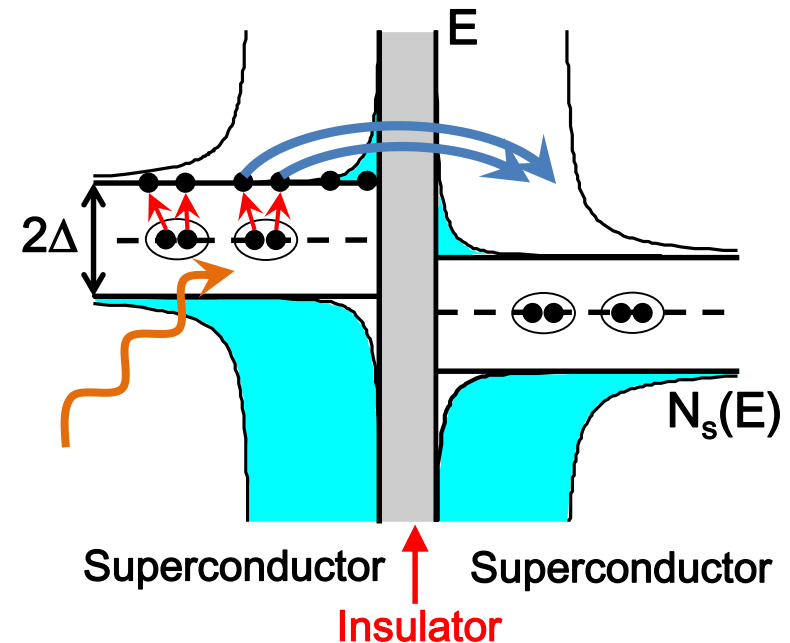
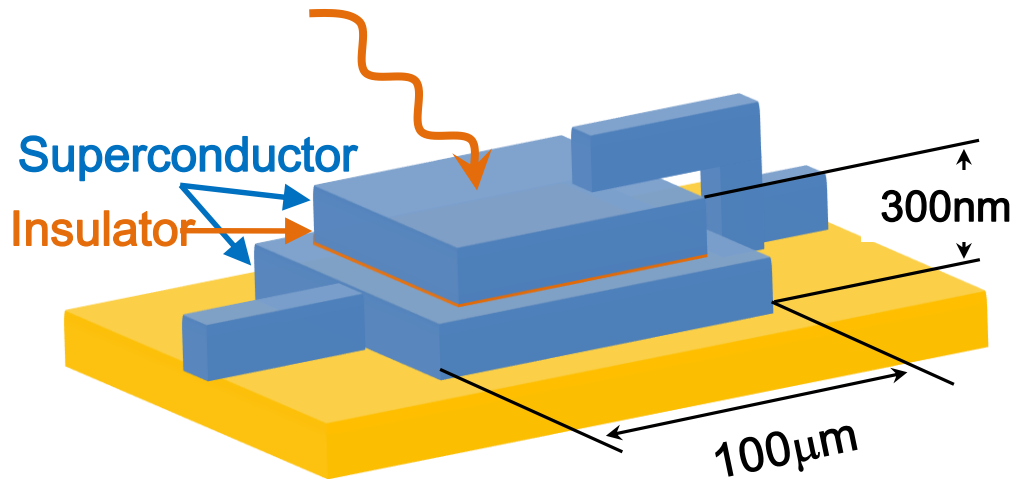
$$\rightarrow \text{NEP} = \epsilon_{\gamma} \sqrt{2f_{\gamma}} \sim 1 \times 10^{-19} \text{ W} / \sqrt{\text{Hz}}$$

We are trying to achieve $\text{NEP} \sim 10^{-19} \text{ W} / \sqrt{\text{Hz}}$ **by using**

- **Superconducting Tunneling Junction detector**
- **Cryogenic amplifier readout**

Superconducting Tunnel Junction (STJ) Detector

- Superconductor / **Insulator** / Superconductor Josephson junction device



Δ : Superconducting gap energy

A constant bias voltage ($|V| < 2\Delta$) is applied across the junction.
A photon absorbed in the superconductor breaks Cooper pairs and creates tunneling current of quasi-particles proportional to the deposited photon energy.

- Much lower gap energy (Δ) than FIR photon → Can detect FIR photon
- Faster response ($\sim \mu\text{s}$) → Suitable for single-photon counting

STJ energy resolution

Signal = Number of quasi-particles

$$N_{q.p.} = G \frac{E_\gamma}{1.7\Delta}$$

Resolution = Statistical fluctuation in number of quasi-particles

$$\sigma_E/E = \sqrt{(1.7\Delta)F/E}$$

→ Smaller superconducting gap energy Δ yields better energy resolution

Δ : Superconducting gap energy
F: fano factor (~ 0.2 for Nb)
E: Photon energy
G: Back-tunneling gain

	Si	Nb	Al	Hf
Tc[K]		9.23	1.20	0.165
Δ [meV]	1100	1.550	0.172	0.020

Tc :SC critical temperature
Need $\sim 1/10T_c$ for practical operation

STJ candidates

Nb/Al-STJ

- Well-established
 - $\Delta \sim 0.6 \text{ meV}$ by the proximity effect from Al
 - Operation temperature $< 400 \text{ mK}$
 - Back-tunnelling gain $G \sim 10$
- $N_{\text{q.p.}} = 25 \text{ meV} / 1.7\Delta \times 10 \sim 250$ $\sigma_E/E \sim 0.1$ for $E = 25 \text{ meV}$
- 25 meV single-photon detection is feasible in principle
- Developing for the rocket experiment

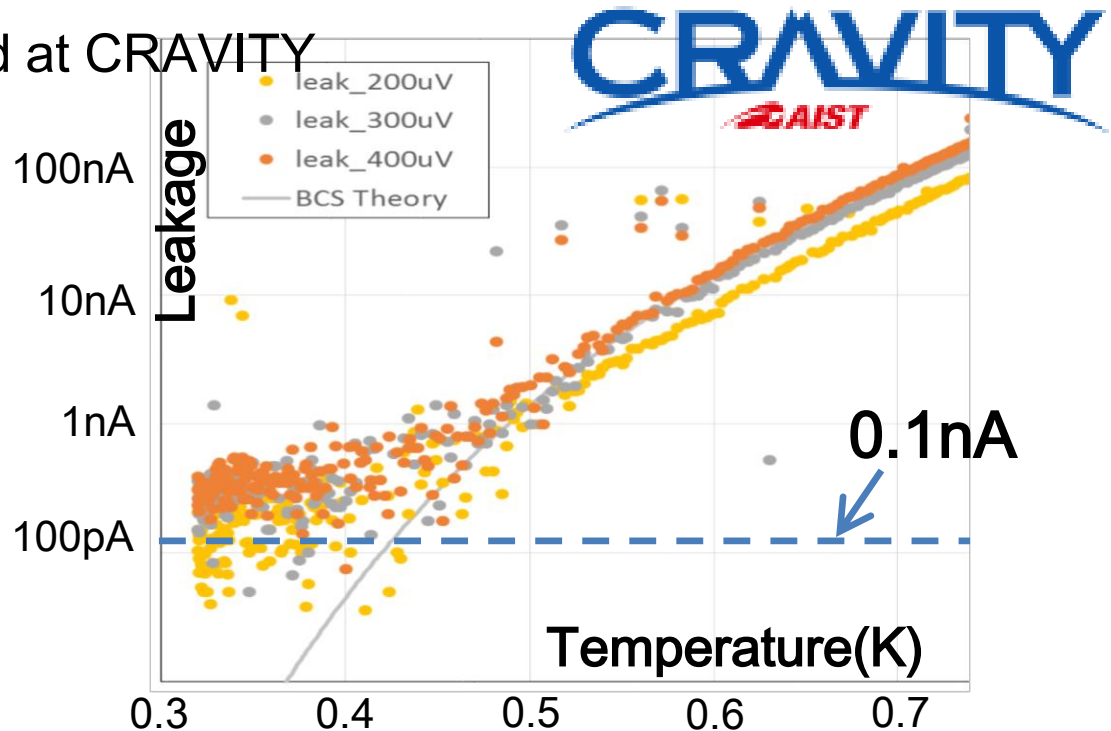
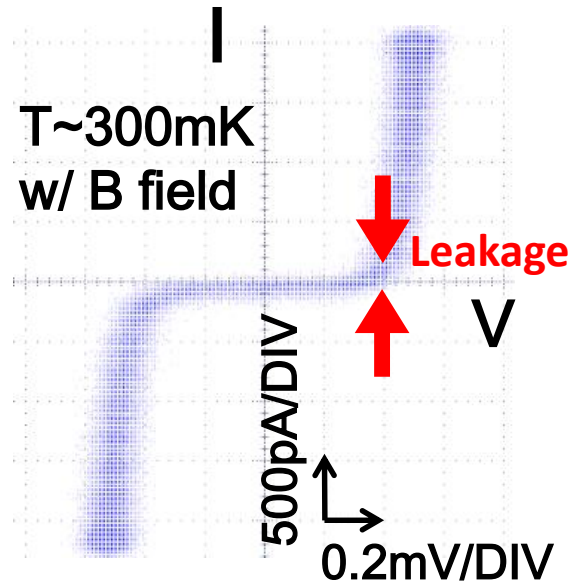
Hf-STJ

K.Takemasa's talk "R&D Status of Hf-STJ"

- Not established as a practical photo-detector yet by any group
- $N_{\text{q.p.}} = 25 \text{ meV} / 1.7\Delta \sim 735$
- 2% energy resolution for a 25 meV single-photon is achievable
if Fano factor < 0.3 for Hf
- Spectrum measurement without a diffraction grating
- Developing for a future satellite experiment

Nb/Al-STJ development at CRAVITY

50 μ m sq. Nb/Al-STJ fabricated at CRAVITY



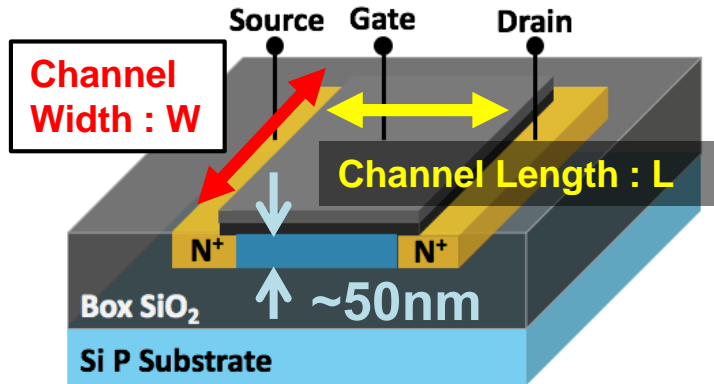
$I_{\text{leak}} \sim 200\text{pA}$ for 50 μ m sq. STJ, and **achieved 50pA for 20 μ m sq.**

→ This satisfies our requirement!

Far-infrared single photon detection is feasible with **this Nb/Al-STJ sensor** and **a cryogenic amplifier** which can be deployed in close proximity to the STJ.

FD-SOI-MOSFET at cryogenic temperature

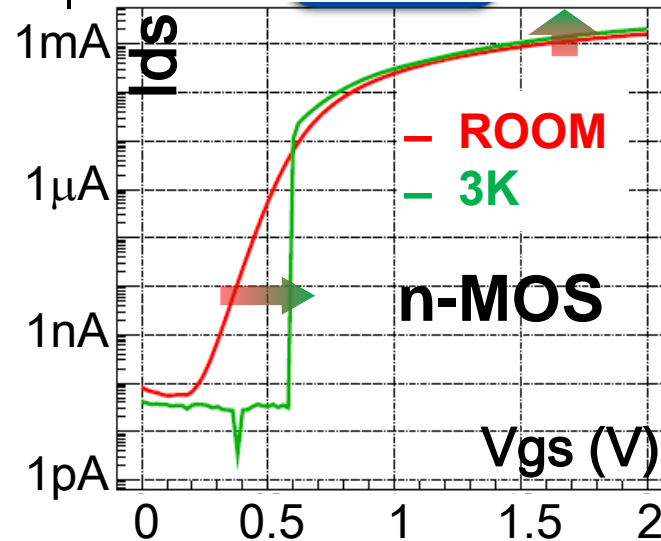
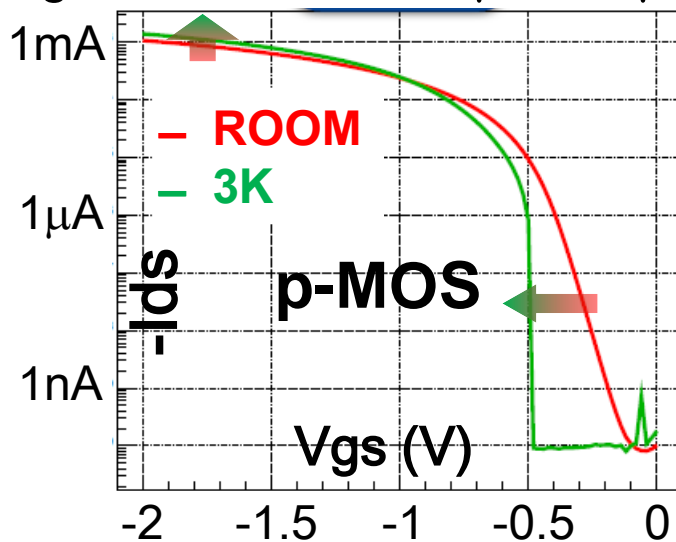
FD-SOI : **F**ully **D**epleted – **S**ilicon **O**n **I**nsulator



- ❑ Very thin channel layer in MOSFET on SiO₂
- ❑ No floating body effect caused by charge accumulation in the body
- ❑ FD-SOI-MOSFET is reported to work at 4K

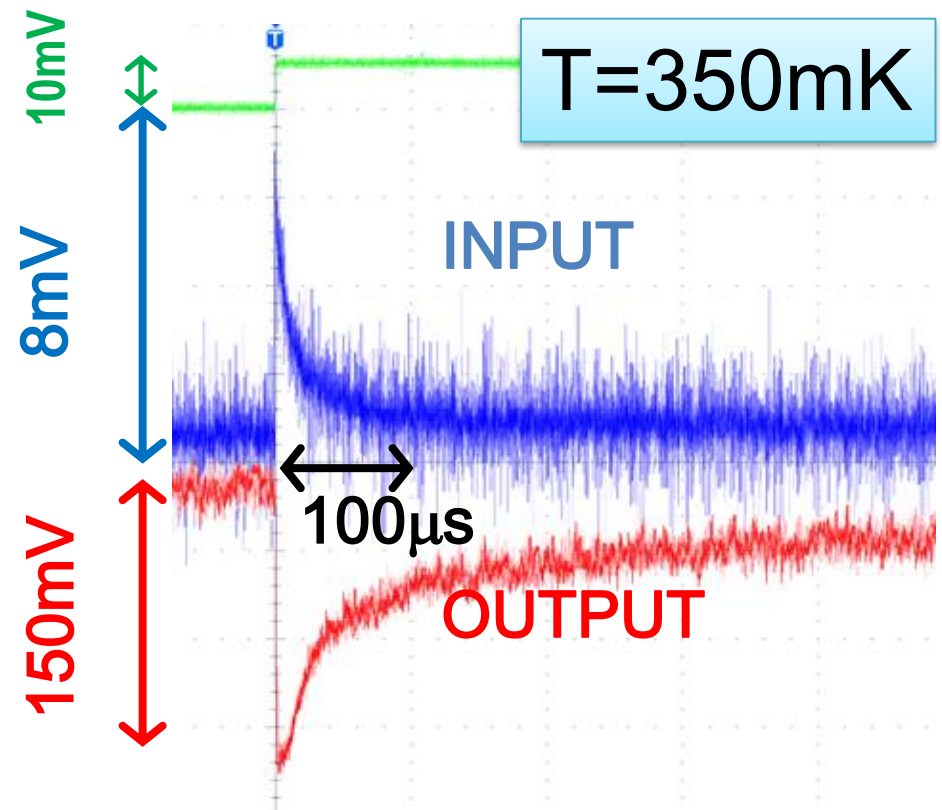
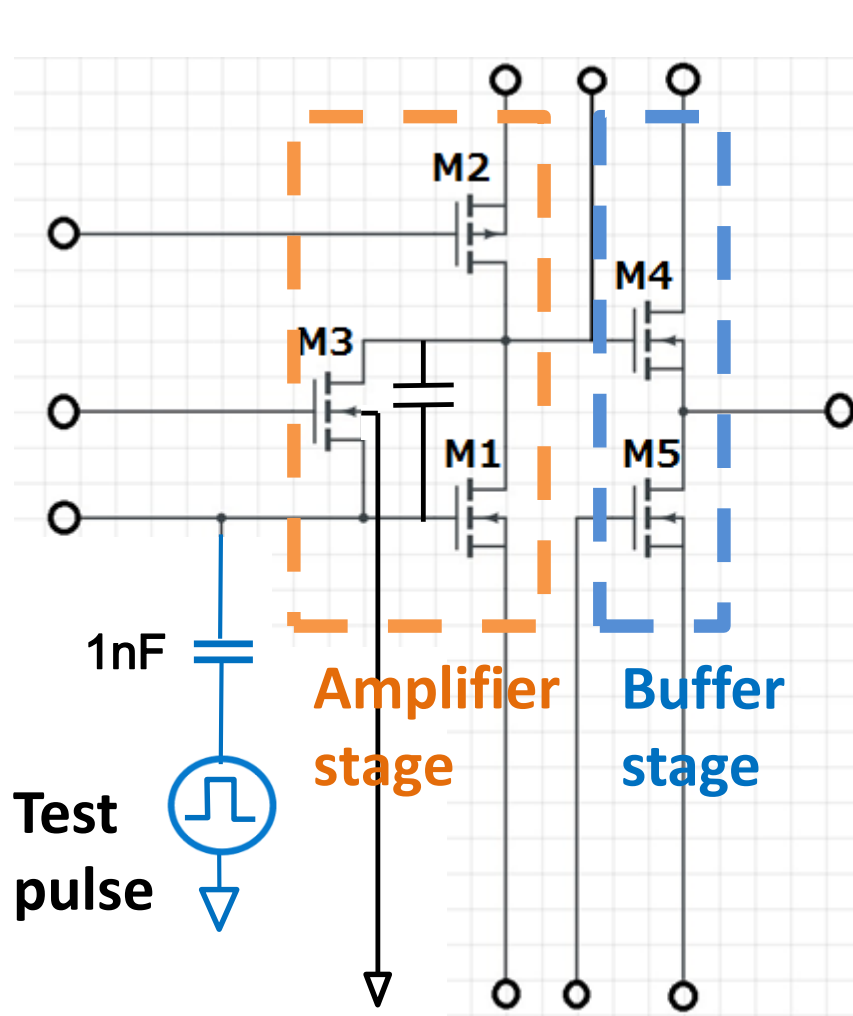
JAXA/ISIS AIPC 1185,286-289(2009)
J Low Temp Phys 167, 602 (2012)

I_d - V_g curve of $W/L=10\mu\text{m}/0.4\mu\text{m}$ at $|V_{ds}|=1.8\text{V}$



Both p-MOS and n-MOS show excellent performance at 3K and below.

SOI prototype amplifier for demonstration test

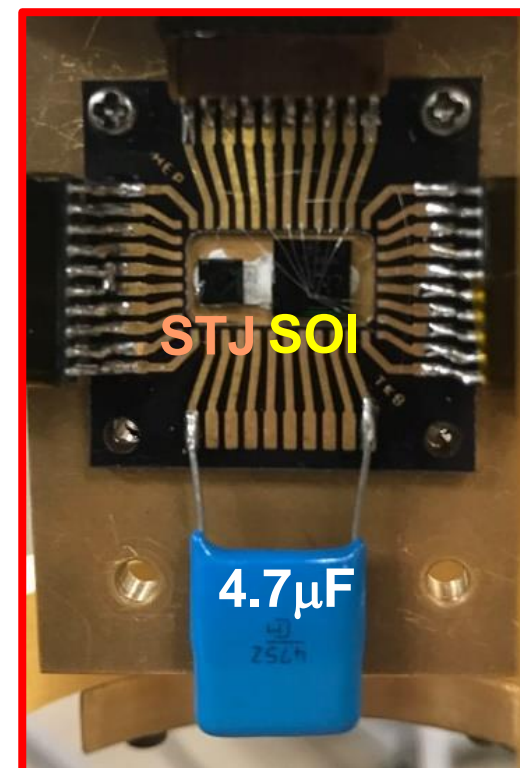
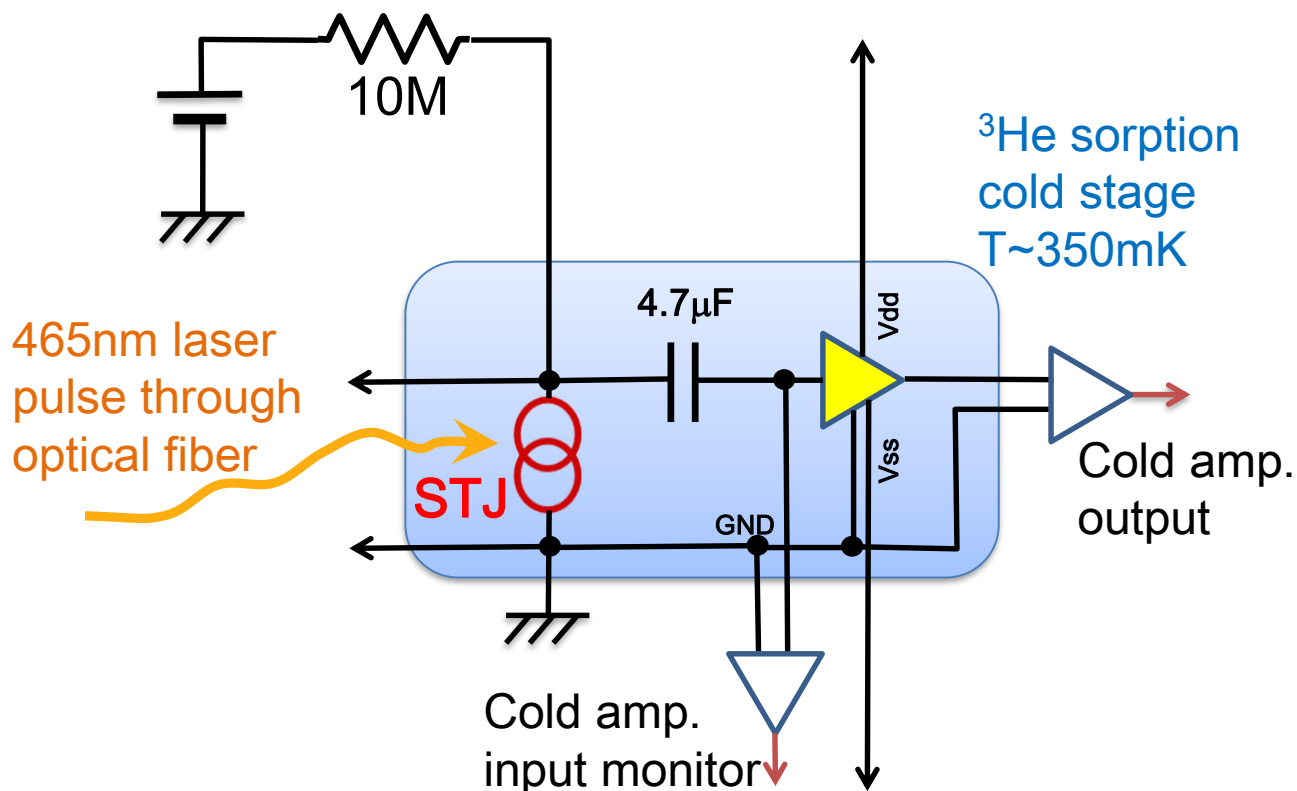


Test pulse input through $C=1\text{nF}$ at $T=3\text{K}$ and 350mK

- Power consumption: $\sim 100\mu\text{W}$
- Output load: $1\text{M}\Omega$ and $\sim 0.5\text{nF}$

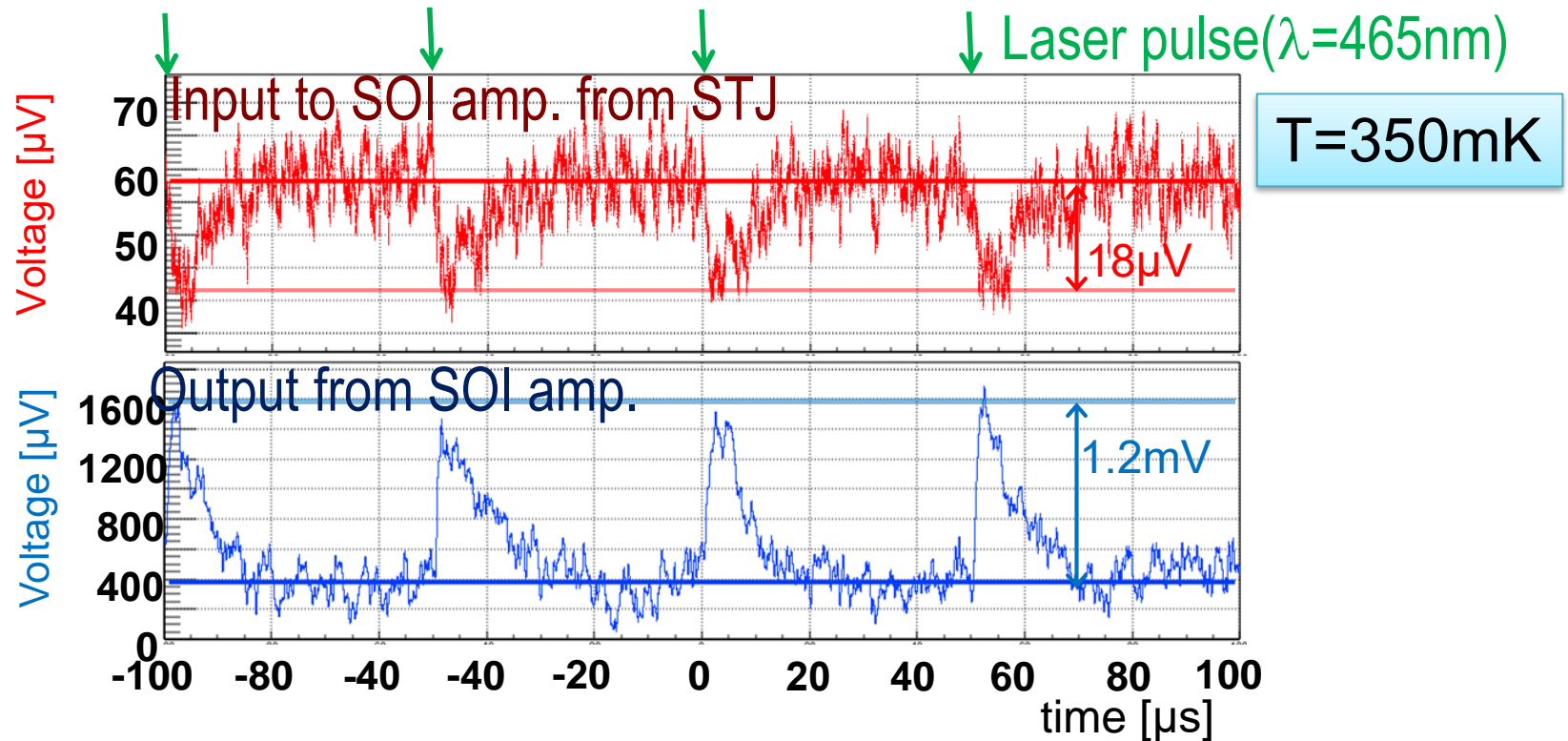
We can compensate the effect of shifts in the thresholds by adjusting bias voltages.

Amplification of STJ response to laser pulse on cold stage



We connect 20 μ m sq. Nb/Al-STJ and SOI amplifier on the cold stage through a capacitance

Amplification of STJ response to laser pulse on cold stage

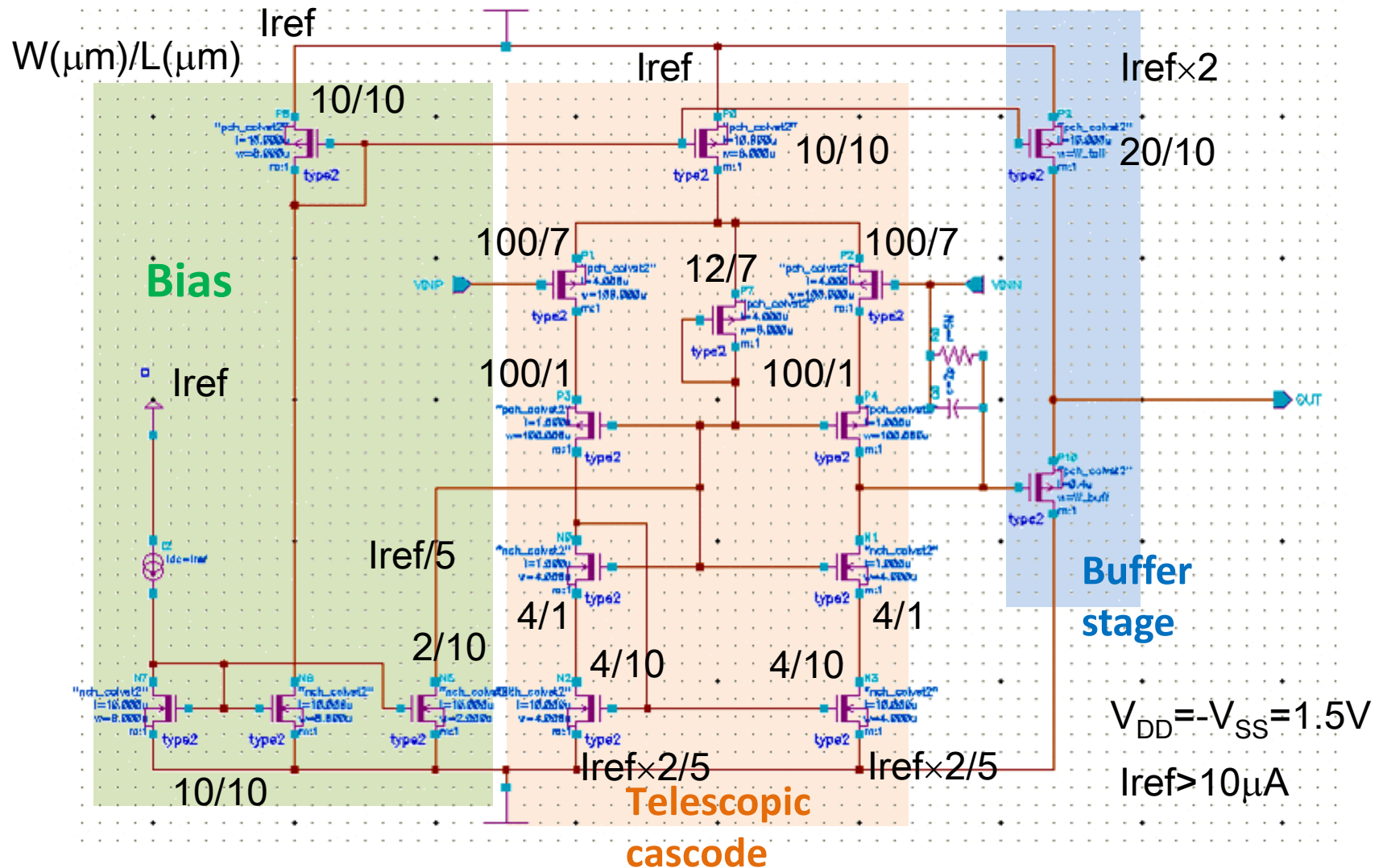


Demonstrated to show amplification of Nb/Al-STJ response to laser pulse by SOI amplifier situated close to STJ at T=350mK

Development of SOI cryogenic amplifier for STJ signal readout is now moving to the stage of design for practical use !

Charge sensitive amplifier design for STJ single photon detection

R.Wakasa's talk



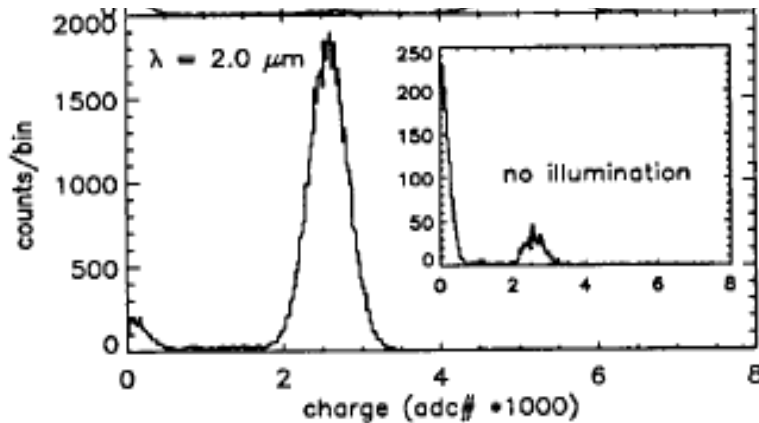
Summary

- We propose a sounding rocket experiment to search for neutrino radiative decay in cosmic neutrino background, and a following satellite experiment .
- Nb/Al-STJ array with a grating for the rocket experiment.
 - Demonstrated STJ signal amplification by a prototype SOI amplifier at $T \sim 350\text{mK}$
 - Now we design and develop SOI cryogenic amplifier for practical use
→ R. Wakasa's talk
- Hf-STJ → K. Takemasa's talk

- C. Asano “Single Photon Detection by Nb/Al-STJ with Cryogenic SOI Amplifier for COBAND experiment”
- K.Nishimura “A Far-Infrared Pulsed Light Source to Calibrate STJ Detectors for COBAND Experiment”
- Y.Takeuchi “Feasibility of sub-GeV mass dark matter search using STJ detector for COBAND experiment”

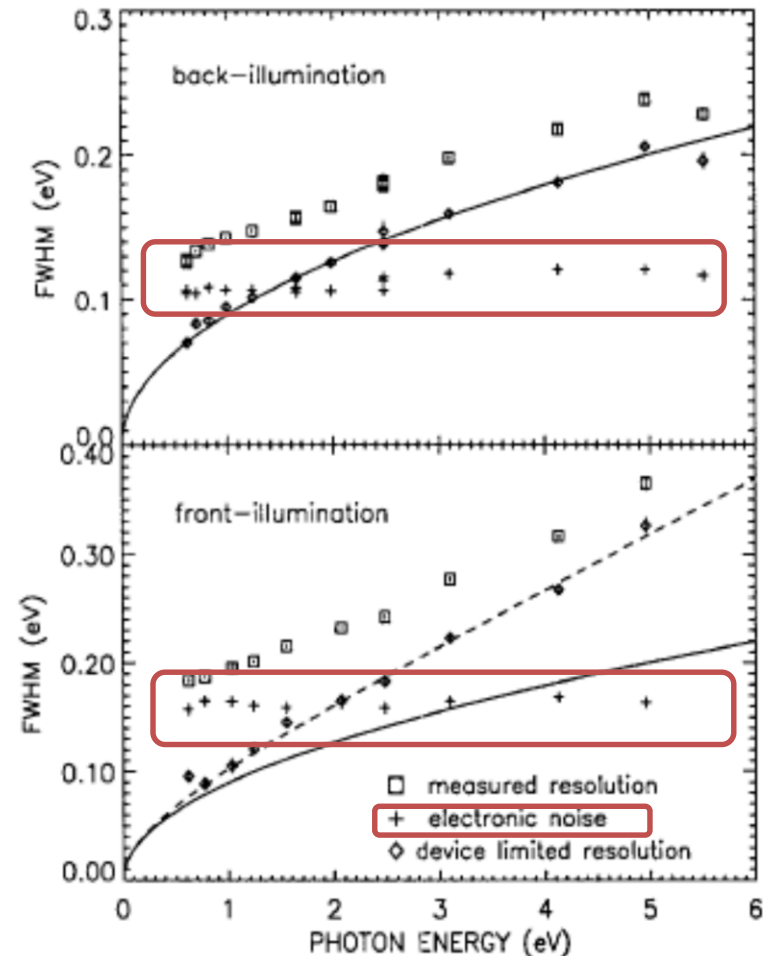
Backup

STJ energy resolution for near infrared photon



P. Verhoeve et. al 1997

- $30\mu\text{m}$ sq. Ta/Al-STJ
- $\Delta E \sim 130\text{meV}$ @ $E=620\text{meV}(\lambda=2\mu\text{m})$
- Charge sensitive amplifier at room temp.
- Electronic noise $\sim 100\text{meV}$



In sub-eV ~ several-eV region, STJ gives the best energy resolution among superconductor based detectors, but limited by readout electronic noise.

Noise Equivalent Power (NEP) Requirements for the photo-detector

- ❑ Neutrino decay ($m_3 = 50 \text{ meV}$, $\tau_\nu = 10^{14} \text{ yrs}$): $I_\nu = 25 \text{ kJy/sr}$ @ $\lambda = 50 \mu\text{m}$

$$P_{ND} = 25 \text{ kJy/sr} \times 8 \times 10^{-8} \text{ sr} \times \pi (15 \text{ cm}/2)^2 \times \Delta\nu \\ = 3.3 \times 10^{-20} \text{ W/8pix}$$

- ❑ Zodiacal emission: $I_\nu = 8 \text{ MJy/sr}$ @ $\lambda = 50 \mu\text{m}$

$$P_{ZE} = 1.1 \times 10^{-17} \text{ W/8pix}$$

- ◆ Shot noise in P_{ZE} integrated over an interval Δt

– Fluctuation in number of photons with energy ϵ_γ : $\sqrt{\epsilon_\gamma P_{ZE} \Delta t}$

$$\frac{NEP}{\sqrt{2\Delta t}} \times \Delta t \ll \sqrt{\epsilon_\gamma P_{ZE} \Delta t} \ll P_{ND} \Delta t$$

→ $\Delta t > 200 \text{ sec}$

→ $NEP \sim 0(10^{-20}) \text{ W}/\sqrt{\text{Hz}}$ for 1pix

Existing FIR photo-detectors

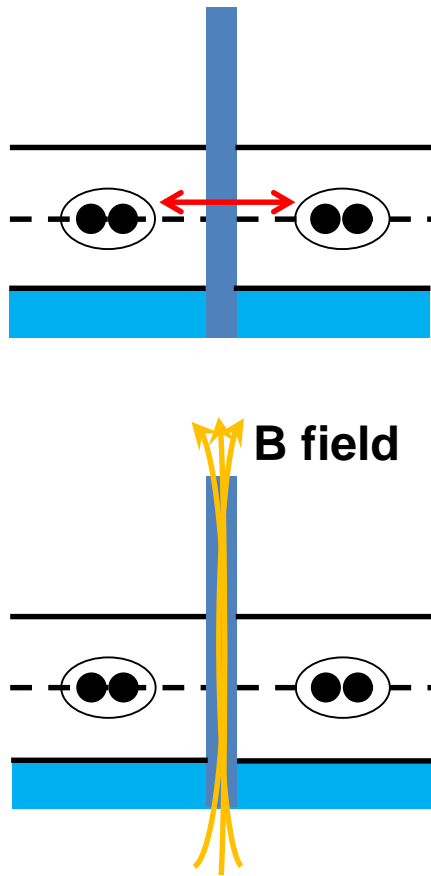
Detectors	$\lambda(\mu\text{m})$	Operation Temp.	NEP ($\text{W}/\text{Hz}^{1/2}$)	
Monolithic Ge:Ga	50-110	2.2K	$\sim 10^{-17}$	Akari-FIS
Stressed Ge:Ga	60-210	0.3K	$\sim 0.9 \times 10^{-17}$	Herschel-PACS

Need **more than 2 orders improvement** from existing photoconductor-based detectors

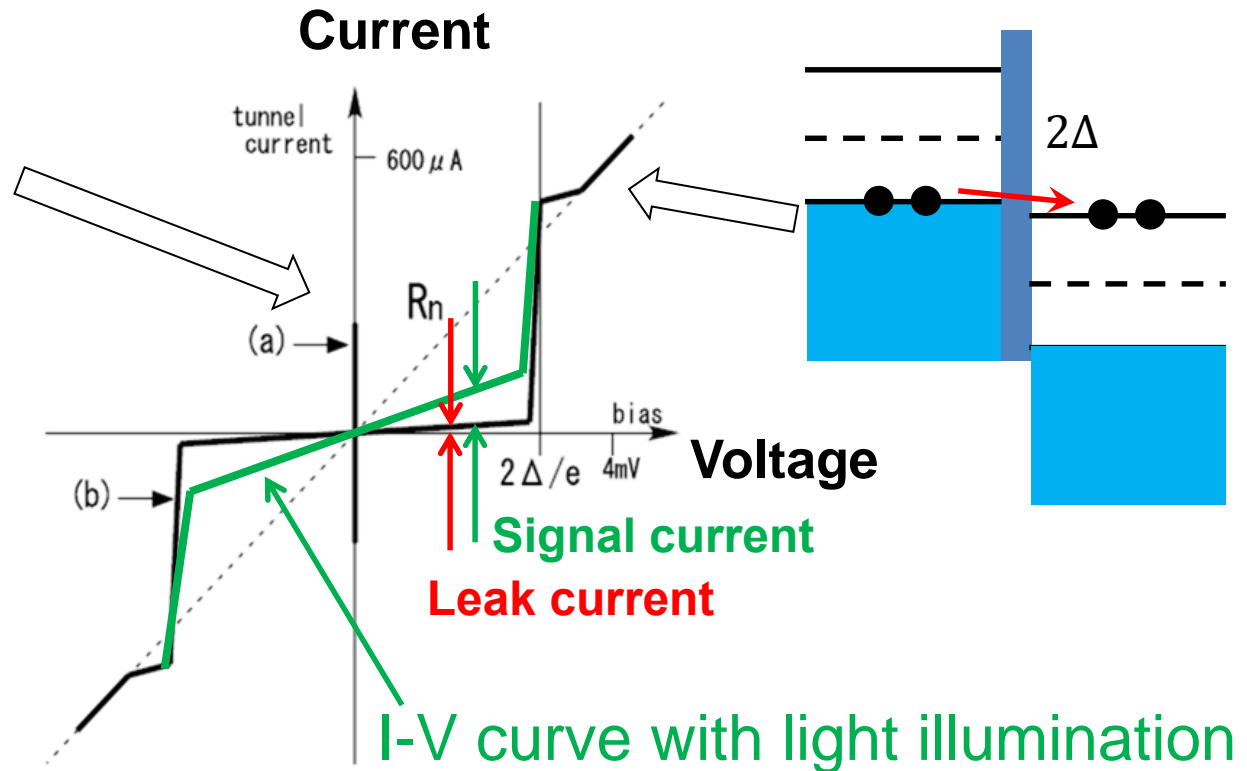
We are trying to achieve $\text{NEP} \sim 0(10^{-20}) \text{ W}/\sqrt{\text{Hz}}$ **by using**

- **Superconducting tunneling junction detector**
- **FIR single-photon counting technique**

STJ current-voltage curve



Tunnel current of Cooper pairs (Josephson current) is suppressed by applying magnetic field

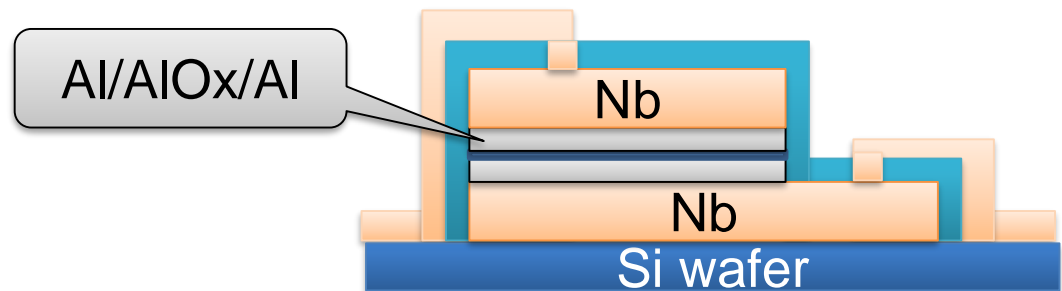


Optical signal readout

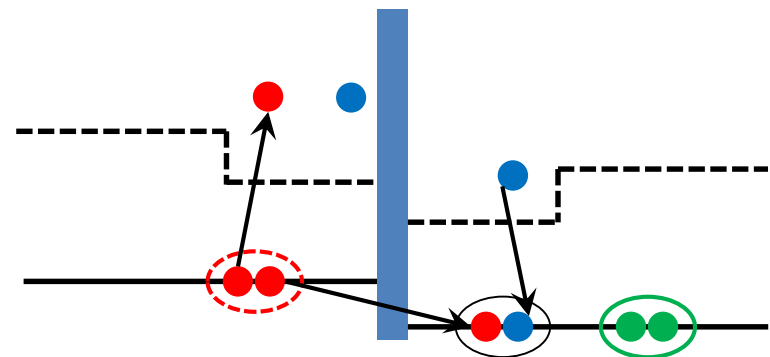
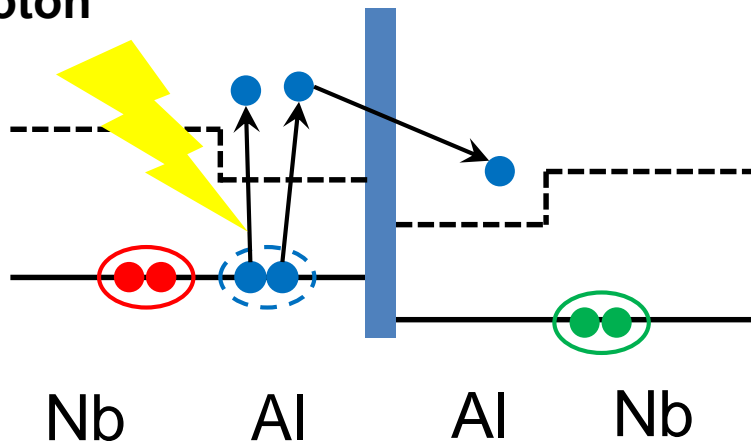
- Apply a constant bias voltage ($|V| < 2\Delta$) across the junction and collect tunneling current of quasi particles created by photons
- ✓ Leak current causes background noise

STJ back-tunneling effect

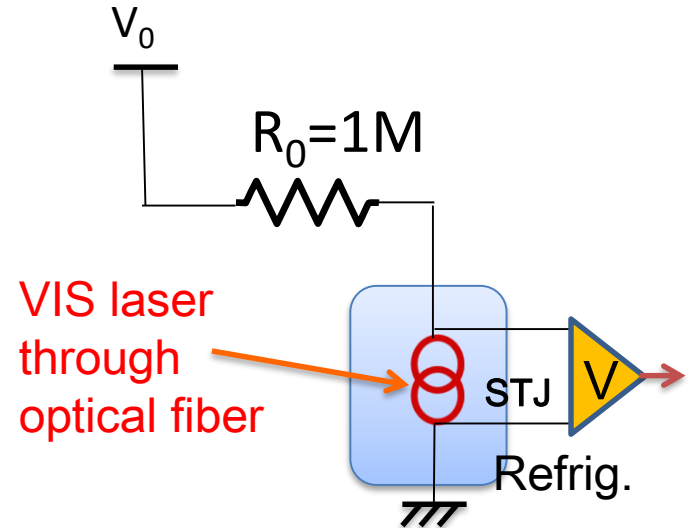
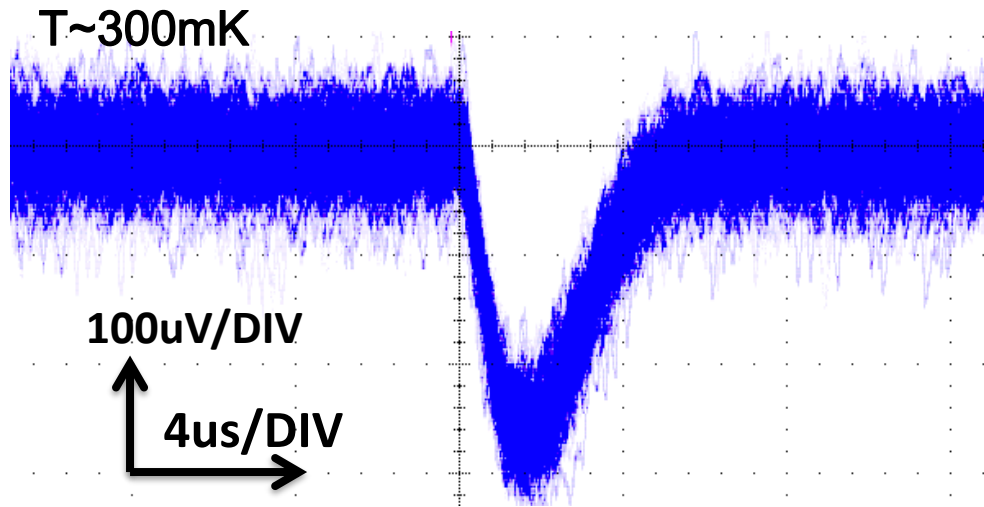
- Bi-layer fabricated with superconductors of different gaps $\Delta_{\text{Nb}} > \Delta_{\text{Al}}$ to enhance quasi-particle density near the barrier
 - Quasi-particle near the barrier can mediate **multiple Cooper pairs**
- Nb/Al-STJ Nb(200nm)/Al(70nm)/AlOx/Al(70nm)/Nb(200nm)
- Gain: ~ 10



Photon



STJ response to pulsed laser

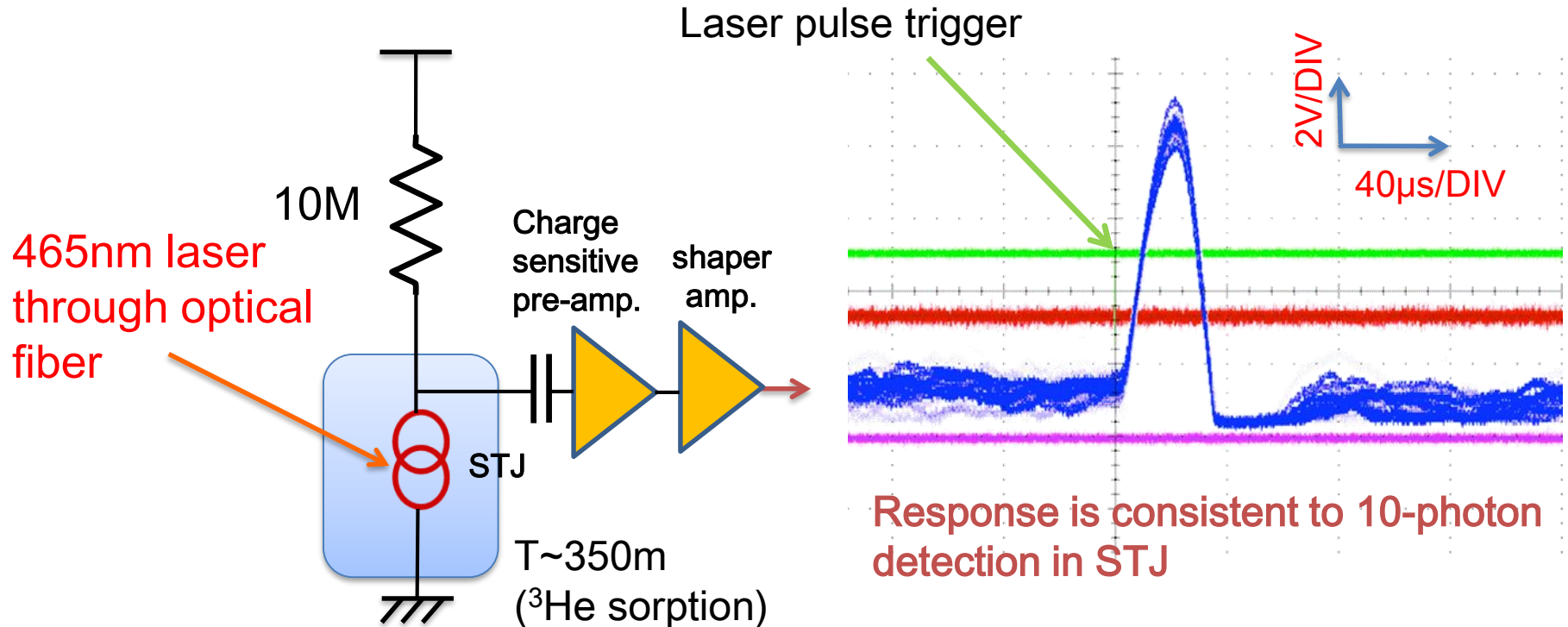


Nb/Al-STJ response to pulsed laser (465nm)
CRAVITY Nb/Al-STJ $100\mu\text{m}$ sq.

Nb/Al-STJ has $\sim 1\mu\text{s}$ response time.

- We can improve NEP by photon counting in $1\mu\text{s}$ integration time
- However we need faster readout system than $f > 1\text{MHz}$

100x100 μm^2 Nb/Al-STJ response to 465nm pulsed laser



We observed NIR-VIS laser pulse **at few-photon level** with a charge-sensitive amplifier placed at the room temperature.

Due to the readout noise, a FIR single-photon detection is not achieved yet.

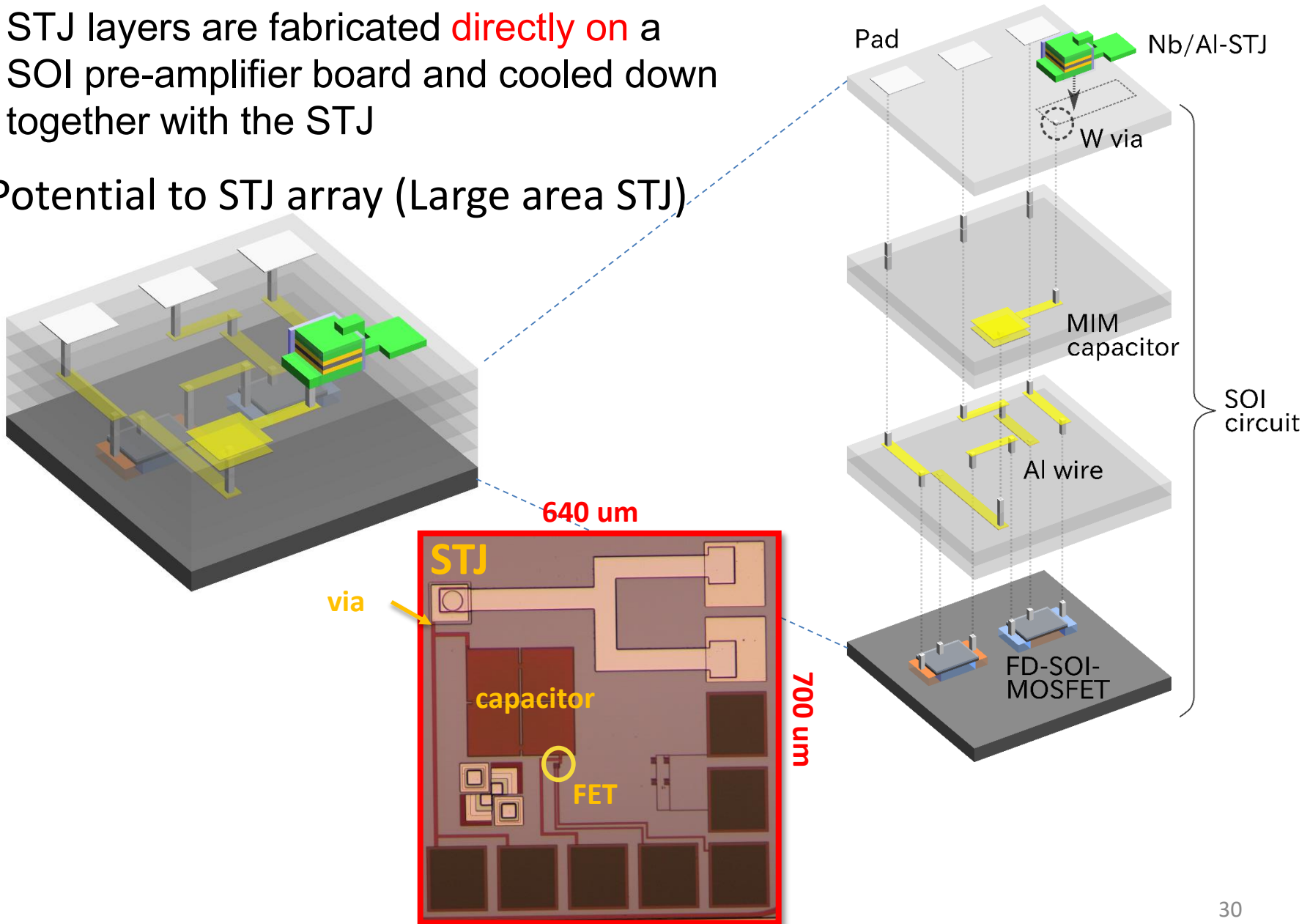
Need ultra-low noise readout system for STJ signal

→ Considering a cryogenic pre-amplifier placed close to STJ

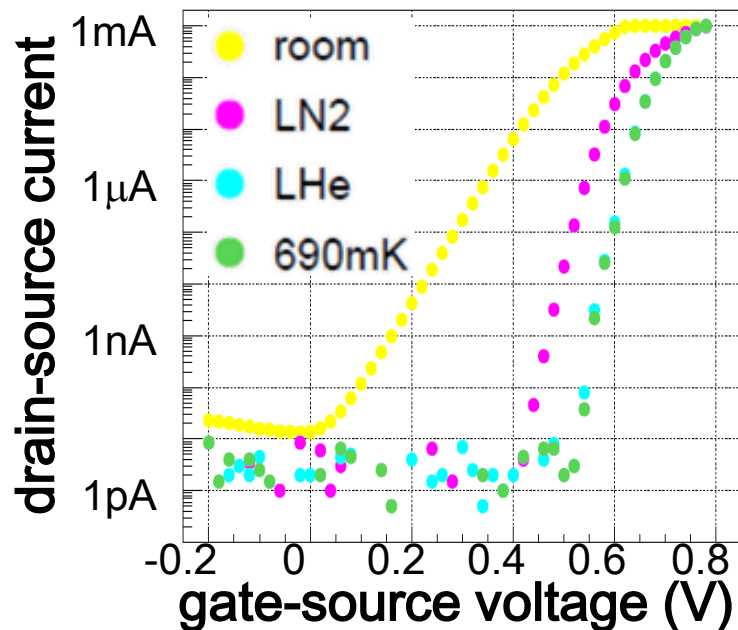
SOI-STJ (STJ directly on SOI) development

- STJ layers are fabricated **directly on** a SOI pre-amplifier board and cooled down together with the STJ

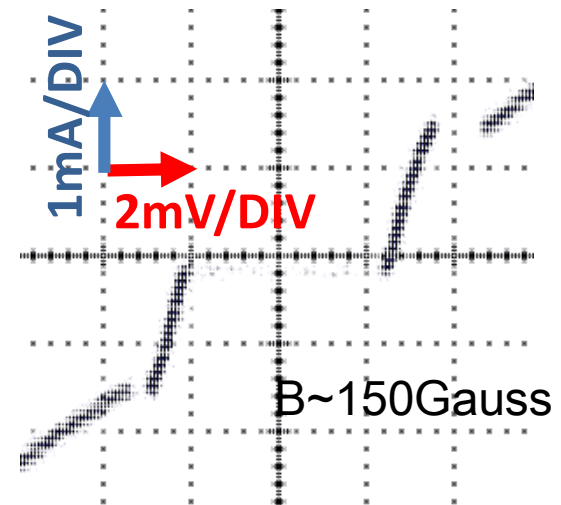
□ Potential to STJ array (Large area STJ)



FD-SOI on which STJ is fabricated



nMOS-FET in FD-SOI wafer on which a STJ is fabricated at KEK



I-V curve of a STJ fabricated at KEK on a FD-SOI wafer

- Both nMOS and pMOS-FET in FD-SOI wafer on which a STJ is fabricated work fine at temperature down below 1K
- Nb/Al-STJ fabricated at KEK on FD-SOI works fine
- We are also developing SOI-STJ where STJ is fabricated at CRAVITY